

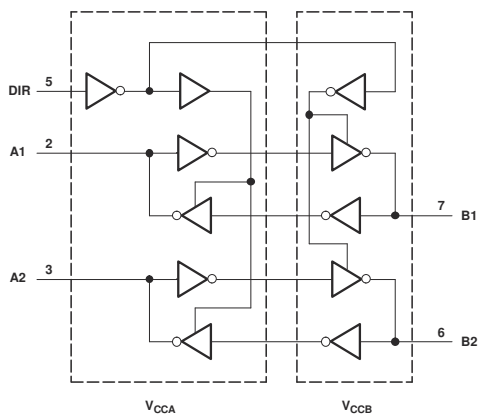
SN74LVC2T45 構成可能なレベル・シフト機能搭載、デュアルビット、デュアル電源バス・トランシーバ

1 特長

- 完全に構成可能なデュアル・レール設計により、1.65V ~ 5.5V の電源電圧の全範囲にわたって各ポートが動作可能
- V_{CC} 絶縁機能: どちらかの V_{CC} 入力が高インピーダンス状態に移行になると、両方のポートが高インピーダンス状態に移行
- V_{CCA} を基準とする DIR 入力回路
- 低い消費電力、最大 I_{CC}: 4μA
- テキサス・インスツルメンツの NanoFree™ パッケージで供給
- 3.3V において ±24mA の出力駆動能力
- I_{off} により部分的パワーダウン・モードでの動作をサポート
- 最大データ・レート:
 - 420Mbps (3.3V から 5V に変換)
 - 210Mbps (3.3V に変換)
 - 140Mbps (2.5V に変換)
 - 75Mbps (1.8V に変換)
- JESD 78、Class II 準拠で 100mA 超のラッチアップ性能
- JESD 22 を上回る ESD 保護
 - 4000V、人体モデル (A114-A)
 - 200V、マシン・モデル (A115-A)
 - 1000V、デバイス帯電モデル (C101)

2 アプリケーション

- パーソナル・エレクトロニクス
- 産業用
- エンタープライズ
- テレコム



機能ブロック図

3 概要

この 2 ビット非反転バストランシーバは、設定可能な 2 本の独立した電源レールを使用します。A ポートは V_{CCA} に追従するように設計されています。V_{CCA} ピンには、1.65V ~ 5.5V の電源電圧を入力できます。B ポートは、V_{CCB} に追従する設計になっています。V_{CCB} ピンには、1.65V ~ 5.5V の電源電圧を入力できます。これにより、1.8V、2.5V、3.3V、5V の任意の電圧ノード間での低電圧双方向変換が可能です。

SN74LVC2T45 は、2 つのデータバス間の非同期通信用に設計されています。方向制御 (DIR) 入力のロジックレベルにより、B ポート出力と A ポート出力のどちらかがアクティブになります。本デバイスは、B ポート出力がアクティブになった場合、A バスから B バスへデータを転送し、A ポート出力がアクティブになった場合、B バスから A バスへデータを転送します。A ポートと B ポートの入力回路はどちらも常にアクティブであるため、これらのポートには論理 High または Low レベルを印加して、I_{CC} と I_{CCZ} が過剰に流れないようにする必要があります。

SN74LVC2T45 は、V_{CCA} が DIR 入力回路に電力を供給するように設計されています。このデバイスは、I_{off} を使用する部分的パワーダウンアプリケーション用の動作が完全に規定されています。I_{off} 回路で出力をディセーブルすることにより、電源切断時にデバイスに電流が逆流して損傷するのを回避できます。

V_{CC} 絶縁機能は、いずれかの V_{CC} 入力が高インピーダンス状態になると、両方のポートが高インピーダンス状態になるよう設計されています。

パッケージ情報

部品番号	パッケージ (1)	パッケージサイズ (2)
SN74LVC2T45	DCT (SM8, 8)	2.95mm × 4mm
	DCU (VSSOP, 8)	2mm × 3.1mm
	YZP (DSBGA, 8)	1.5mm × 0.5mm

- 詳細については、[セクション 11](#) を参照してください。
- パッケージサイズ (長さ × 幅) は公称値であり、該当する場合はピンも含まれます。



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4 Pin Configuration and Functions

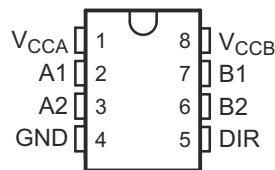


図 4-1. DCT or DCU Package, 8-Pin SM8 or VSSOP (Top View)

表 4-1. Pin Functions: DCT, DCU

PIN		TYPE ⁽¹⁾	DESCRIPTION
NAME	NO.		
V_{CCA}	1	P	A-port supply voltage. $1.65V \leq V_{CCA} \leq 5.5V$
A1	2	I/O	Input/output A1. Referenced to V_{CCA}
A2	3	I/O	Input/output A2. Referenced to V_{CCA}
GND	4	G	Ground
DIR	5	I	Direction control signal
B2	6	I/O	Input/output B2. Referenced to V_{CCB}
B1	7	I/O	Input/output B1. Referenced to V_{CCB}
V_{CCB}	8	P	B-port supply voltage. $1.65V \leq V_{CCB} \leq 5.5V$

(1) I = input, O = output, P = power, G = ground

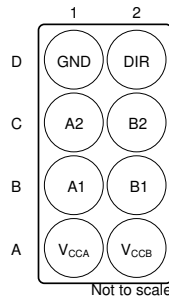


図 4-2. YZP Package, 8-Pin DSGBA (Bottom View)

表 4-2. Pin Functions: YZP

PIN		TYPE ⁽¹⁾	DESCRIPTION
NO.	NAME		
A1	V _{CCA}	P	A-port supply voltage. $1.65V \leq V_{CCA} \leq 5.5V$
A2	V _{CCB}	P	B-port supply voltage. $1.65V \leq V_{CCB} \leq 5.5V$
B1	A1	I/O	Input/output A1. Referenced to V _{CCA}
B2	B1	I/O	Input/output B1. Referenced to V _{CCB}
C1	A2	I/O	Input/output A2. Referenced to V _{CCA}
C2	B2	I/O	Input/output B2. Referenced to V _{CCB}
D1	GND	G	Ground
D2	DIR	I	Direction control signal

(1) I = input, O = output, P = power, G = ground

5 Specifications

5.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted)⁽¹⁾

		MIN	MAX	UNIT
V _{CCA}	Supply voltage	-0.5	6.5	V
V _{CCB}				
V _I	Input voltage ⁽²⁾	-0.5	6.5	V
V _O	Voltage range applied to any output in the high-impedance or power-off state ⁽²⁾	-0.5	6.5	V
V _O	Voltage range applied to any output in the high or low state ^{(2) (3)}	A port	V _{CCA} + 0.5	V
		B port	V _{CCB} + 0.5	
I _{IK}	Input clamp current	V _I < 0	-50	mA
I _{OK}	Output clamp current	V _O < 0	-50	mA
I _O	Continuous output current	-50	50	mA
	Continuous current through V _{CC} or GND	-100	100	mA
T _J	Junction temperature		150	°C
T _{stg}	Storage temperature	-65	150	°C

- (1) Stresses beyond those listed under *Absolute Maximum Ratings* may cause permanent damage to the device. These are stress ratings only, which do not imply functional operation of the device at these or any other conditions beyond those indicated under *Recommended Operating Conditions*. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.
- (2) The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
- (3) The value of V_{CC} is provided in the *Recommended Operating Conditions* table.

5.2 ESD Ratings

		VALUE	UNIT
V _(ESD)	Electrostatic discharge	Human body model (HBM), per ANSI/ESDA/JEDEC JS-001 ¹	±4000
		Charged device model (CDM), per ANSI/ESDA/JEDEC JS-002 ²	±1000

- (1) JEDEC document JEP155 states that 500V HBM allows safe manufacturing with a standard ESD control process.
- (2) JEDEC document JEP157 states that 250V CDM allows safe manufacturing with a standard ESD control process.

5.3 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted)^{(1) (2) (3)}

		V _{CCI}	V _{CCO}	MIN	MAX	UNIT
V _{CCA}	Supply voltage			1.65	5.5	V
V _{CCB}				1.65	5.5	
V _{IH}	High-level input voltage	Data inputs ⁽⁴⁾	1.65V to 1.95V	V _{CCI} × 0.65		V
			2.3V to 2.7V	1.7		
			3V to 3.6V	2		
			4.5V to 5.5V	V _{CCI} × 0.7		
V _{IL}	Low-level input voltage	Data inputs ⁽⁴⁾	1.65V to 1.95V	V _{CCI} × 0.35		V
			2.3V to 2.7V	0.7		
			3V to 3.6V	0.8		
			4.5V to 5.5V	V _{CCI} × 0.3		
V _{IH}	High-level input voltage	DIR (referenced to V _{CCA}) ⁽⁵⁾	1.65V to 1.95V	V _{CCA} × 0.65		V
			2.3V to 2.7V	1.7		
			3V to 3.6V	2		
			4.5V to 5.5V	V _{CCA} × 0.7		

5.3 Recommended Operating Conditions (続き)

over operating free-air temperature range (unless otherwise noted)^{(1) (2) (3)}

		V _{CCI}	V _{CCO}	MIN	MAX	UNIT
V _{IL}	Low-level input voltage	DIR (referenced to V _{CCA}) ⁽⁵⁾	1.65V to 1.95V		V _{CCA} × 0.35	V
			2.3V to 2.7V		0.7	
			3V to 3.6V		0.8	
			4.5V to 5.5V		V _{CCA} × 0.3	
V _I	Input voltage			0	5.5	V
V _O	Output voltage			0	V _{CCO}	V
I _{OH}	High-level output current		1.65V to 1.95V		–4	mA
			2.3V to 2.7V		–8	
			3V to 3.6V		–24	
			4.5V to 5.5V		–32	
I _{OL}	Low-level output current		1.65V to 1.95V		4	mA
			2.3V to 2.7V		8	
			3V to 3.6V		24	
			4.5V to 5.5V		32	
Δt/Δv	Input transition rise or fall rate	Data inputs	1.65V to 1.95V		20	ns/V
			2.3V to 2.7V		20	
			3V to 3.6V		10	
			4.5V to 5.5V		5	
		Control input	1.65V to 5.5V		5	
T _A	Operating free-air temperature			–40	85	°C

- (1) V_{CCI} is the V_{CC} associated with the input port.
- (2) V_{CCO} is the V_{CC} associated with the output port.
- (3) All unused data inputs of the device must be held at V_{CCI} or GND for proper device operation. See [Implications of Slow or Floating CMOS Inputs](#), SCBA004.
- (4) For V_{CCI} values not specified in the data sheet, V_{IH} min = V_{CCI} × 0.7V, V_{IL} max = V_{CCI} × 0.3V.
- (5) For V_{CCI} values not specified in the data sheet, V_{IH} min = V_{CCA} × 0.7V, V_{IL} max = V_{CCA} × 0.3V.

5.4 Thermal Information

THERMAL METRIC ⁽¹⁾		SN74LVC2T45			UNIT
		DCU	DCT	YZP	
		8 PINS			
R _{θJA}	Junction-to-ambient thermal resistance	246.4	195.3	105.8	°C/W
R _{θJC(top)}	Junction-to-case (top) thermal resistance	95.4	106	1.6	°C/W
R _{θJB}	Junction-to-board thermal resistance	157.8	110.8	10.8	°C/W
Ψ _{JT}	Junction-to-top characterization parameter	37	38.3	3.1	°C/W
Ψ _{JB}	Junction-to-board characterization parameter	156.9	109.3	10.8	°C/W

- (1) For more information about traditional and new thermal metrics, see the [Semiconductor and IC Package Thermal Metrics](#) application report.

5.5 Electrical Characteristics

over recommended operating free-air temperature range (unless otherwise noted)^{1 2}

PARAMETER	TEST CONDITIONS		V _{CCA}	V _{CCB}	T _A = 25°C			–40°C to +85°C		UNIT
					MIN	TYP	MAX	MIN	MAX	
V _{OH}	I _{OH} = –100μA		1.65V to 4.5V	1.65V to 4.5V				V _{CCO} – 0.1		V
	I _{OH} = –4mA		1.65V	1.65V				1.2		
	I _{OH} = –8mA		2.3V	2.3V				1.9		
	I _{OH} = –24mA		3V	3V				2.4		
	I _{OH} = –32mA		4.5V	4.5V				3.8		
V _{OL}	I _{OL} = 100μA		1.65V to 4.5V	1.65V to 4.5V				0.1		V
	I _{OL} = 4mA		1.65V	1.65V				0.45		
	I _{OL} = 8mA		2.3V	2.3V				0.3		
	I _{OL} = 24mA		3V	3V				0.55		
	I _{OL} = 32mA		4.5V	4.5V				0.55		
I _I	DIR	V _I = V _{CCA} or GND	1.65V to 5.5V	1.65V to 5.5V				±1	±2	μA
I _{off}	A port	V _I or V _O = 0 to 5.5V	0V	0 to 5.5V				±1	±2	μA
	B port		0 to 5.5V	0V				±1	±2	
I _{OZ}	A or B port	V _O = V _{CCO} or GND	1.65V to 5.5V	1.65V to 5.5V				±1	±2	μA
I _{CCA}	V _I = V _{CCI} or GND, I _O = 0		1.65V to 5.5V	1.65V to 5.5V					3	μA
			5V	0V					2	
			0V	5V					–2	
I _{CCB}	V _I = V _{CCI} or GND, I _O = 0		1.65V to 5.5V	1.65V to 5.5V					3	μA
			5V	0V					–2	
			0V	5V					2	
I _{CCA} + I _{CCB} (see 表 8-4)	V _I = V _{CCI} or GND, I _O = 0		1.65V to 5.5V	1.65V to 5.5V					4	μA
ΔI _{CCA}	A port	One A port at V _{CCA} – 0.6V, DIR at V _{CCA} , B port = open	3V to 5.5V	3V to 5.5V					50	μA
	DIR	DIR at V _{CCA} – 0.6V, B port = open, A port at V _{CCA} or GND							50	
ΔI _{CCB}	B port	One B port at V _{CCB} – 0.6V, DIR at GND, A port = open	3V to 5.5V	3V to 5.5V					50	μA
C _I	DIR	V _I = V _{CCA} or GND	3.3V	3.3V			2.5			pF
C _{io}	A or B port	V _O = V _{CCA/B} or GND	3.3V	3.3V			6			pF

(1) V_{CCO} is the V_{CC} associated with the output port.

(2) V_{CCI} is the V_{CC} associated with the input port.

5.6 Switching Characteristics: $V_{CCA} = 1.8V \pm 0.15V$

over recommended operating free-air temperature range, $V_{CCA} = 1.8V \pm 0.15V$ (unless otherwise noted) (see [Figure 6-1](#))

PARAMETER	FROM (INPUT)	TO (OUTPUT)	$V_{CCB} = 1.8V \pm 0.15V$		$V_{CCB} = 2.5V \pm 0.2V$		$V_{CCB} = 3.3V \pm 0.3V$		$V_{CCB} = 5V \pm 0.5V$		UNIT
			MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
t_{PLH}	A	B	3	17.7	2.2	10.3	1.7	8.3	1.4	7.2	ns
t_{PHL}			2.8	14.3	2.2	8.5	1.8	7.1	1.7	7	
t_{PLH}	B	A	3	17.7	2.3	16	2.1	15.5	1.9	15.1	ns
t_{PHL}			2.8	14.3	2.1	12.9	2	12.6	1.8	12.2	
t_{PHZ}	DIR	A	5.5	30.9	5.5	30.5	5.5	30.5	5.5	29.3	ns
t_{PLZ}			4.3	19.7	4.2	19.6	4.1	19.5	4	19.4	
t_{PHZ}	DIR	B	6	27.9	5	14.9	5	11.3	4.1	8.6	ns
t_{PLZ}			5	19.5	3.9	12.6	4.3	9.7	2.1	7.1	
t_{PZH}^1	DIR	A	37.2		28.6		25.2		22.2		ns
t_{PZL}^1			42.2		27.8		23.9		20.8		
t_{PZH}^1	DIR	B	37.4		29.9		27.8		26.6		ns
t_{PZL}^1			45.2		39		37.6		36.3		

(1) The enable time is a calculated value, derived using the formula shown in the [Enable Times](#) section.

5.7 Switching Characteristics: $V_{CCA} = 2.5V \pm 0.2V$

over recommended operating free-air temperature range, $V_{CCA} = 2.5V \pm 0.2V$ (unless otherwise noted) (see [Figure 6-1](#))

PARAMETER	FROM (INPUT)	TO (OUTPUT)	$V_{CCB} = 1.8V \pm 0.15V$		$V_{CCB} = 2.5V \pm 0.2V$		$V_{CCB} = 3.3V \pm 0.3V$		$V_{CCB} = 5V \pm 0.5V$		UNIT
			MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
t_{PLH}	A	B	2.3	16	1.5	8.5	1.3	6.4	1.1	5.1	ns
t_{PHL}			2.1	12.9	1.4	7.5	1.3	5.4	0.9	4.6	
t_{PLH}	B	A	2.2	10.3	1.5	8.5	1.4	8	1	7.5	ns
t_{PHL}			2.2	8.5	1.4	7.5	1.3	7	0.9	6.2	
t_{PHZ}	DIR	A	4.2	17.1	4.2	16.8	4.1	16.8	4.1	16.5	ns
t_{PLZ}			3.2	12.6	3.2	12.5	3.2	12.3	3	12.3	
t_{PHZ}	DIR	B	6	27.9	4.7	13.9	4.7	10.5	3.5	7.6	ns
t_{PLZ}			4.2	18.9	3.6	11.2	3.6	8.9	1.4	6.2	
t_{PZH}^1	DIR	A	29.2		19.7		16.9		13.7		ns
t_{PZL}^1			36.4		21.4		17.5		13.8		
t_{PZH}^1	DIR	B	28.6		21		18.7		17.4		ns
t_{PZL}^1			30		24.3		22.2		21.1		

(1) The enable time is a calculated value, derived using the formula shown in the [Enable Times](#) section.

5.8 Switching Characteristics: $V_{CCA} = 3.3V \pm 0.3V$

over recommended operating free-air temperature range, $V_{CCA} = 3.3V \pm 0.3V$ (unless otherwise noted) (see [6-1](#))

PARAMETER	FROM (INPUT)	TO (OUTPUT)	$V_{CCB} = 1.8V \pm 0.15V$		$V_{CCB} = 2.5V \pm 0.2V$		$V_{CCB} = 3.3V \pm 0.3V$		$V_{CCB} = 5V \pm 0.5V$		UNIT
			MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
t_{PLH}	A	B	2.1	15.5	1.4	8	0.7	5.6	0.7	4.4	ns
t_{PHL}			2	12.6	1.3	7	0.8	5	0.7	4	
t_{PLH}	B	A	1.7	8.3	1.3	6.4	0.7	5.8	0.6	5.4	ns
t_{PHL}			1.8	7.1	1.3	5.4	0.8	5	0.7	4.5	
t_{PHZ}	DIR	A	4.5	10.9	4.5	10.8	4.4	10.8	4.4	10.4	ns
t_{PLZ}			3.4	8.4	3.7	8.4	3.9	8.1	3.3	7.8	
t_{PHZ}	DIR	B	5.7	27.3	4.7	13.7	4.7	10.4	2.9	7.4	ns
t_{PLZ}			4.5	17.7	3.5	11.3	4.3	8.3	1	5.6	
t_{PZH}^1	DIR	A	26		17.7		14.1		11		ns
t_{PZL}^1			34.4		19.1		15.4		11.9		
t_{PZH}^1	DIR	B	23.9		16.4		13.9		12.2		ns
t_{PZL}^1			23.5		17.8		15.8		14.4		

(1) The enable time is a calculated value, derived using the formula shown in the [Enable Times](#) section.

5.9 Switching Characteristics: $V_{CCA} = 5V \pm 0.5V$

over recommended operating free-air temperature range, $V_{CCA} = 5V \pm 0.5V$ (unless otherwise noted) (see [6-1](#))

PARAMETER	FROM (INPUT)	TO (OUTPUT)	$V_{CCB} = 1.8V \pm 0.15V$		$V_{CCB} = 2.5V \pm 0.2V$		$V_{CCB} = 3.3V \pm 0.3V$		$V_{CCB} = 5V \pm 0.5V$		UNIT
			MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
t_{PLH}	A	B	1.9	15.1	1	7.5	0.6	5.4	0.5	3.9	ns
t_{PHL}			1.8	12.2	0.9	6.2	0.7	4.5	0.5	3.5	
t_{PLH}	B	A	1.4	7.2	1	5.1	0.7	4.4	0.5	3.9	ns
t_{PHL}			1.7	7	0.9	4.6	0.7	4	0.5	3.5	
t_{PHZ}	DIR	A	2.9	8.2	2.9	7.9	2.8	7.9	2.2	7.8	ns
t_{PLZ}			1.4	6.9	1.3	6.7	0.7	6.7	0.7	6.6	
t_{PHZ}	DIR	B	5.8	26.1	4.4	13.9	4.4	10.1	1.3	7.3	ns
t_{PLZ}			4.7	16.9	3.3	11	4	7.7	1	5.6	
t_{PZH}^1	DIR	A	24.1		16.1		12.1		9.5		ns
t_{PZL}^1			33.1		18.5		14.1		10.8		
t_{PZH}^1	DIR	B	22		14.2		12.1		10.5		ns
t_{PZL}^1			20.4		14.1		12.4		11.3		

(1) The enable time is a calculated value, derived using the formula shown in the [Enable Times](#) section.

5.10 Operating Characteristics

$T_A = 25^\circ\text{C}$

PARAMETER		TEST CONDITIONS	$V_{CCA} =$ $V_{CCB} = 1.8\text{V}$	$V_{CCA} =$ $V_{CCB} = 2.5\text{V}$	$V_{CCA} =$ $V_{CCB} = 3.3\text{V}$	$V_{CCA} =$ $V_{CCB} = 5\text{V}$	UNIT
			TYP	TYP	TYP	TYP	
C_{pdA} (1)	A-port input, B-port output	$C_L = 0\text{pF}$, $f = 10\text{MHz}$, $t_r = t_f = 1\text{ns}$	3	4	4	4	pF
	B-port input, A-port output		18	19	20	21	
C_{pdB} (1)	A-port input, B-port output	$C_L = 0\text{pF}$, $f = 10\text{MHz}$, $t_r = t_f = 1\text{ns}$	18	19	20	21	pF
	B-port input, A-port output		3	4	4	4	

(1) Power dissipation capacitance per transceiver.

5.11 Typical Characteristics

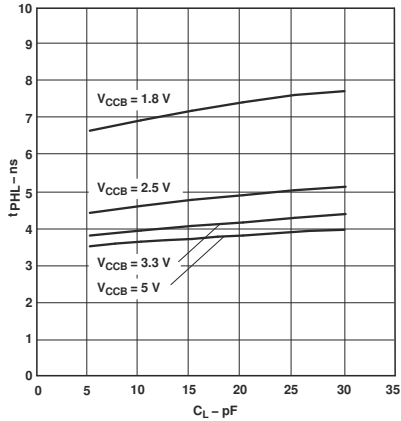


図 5-1. Typical Propagation Delay of High-to-Low (A to B) vs Load Capacitance $T_A = 25^\circ\text{C}$, $V_{CCA} = 1.8\text{V}$

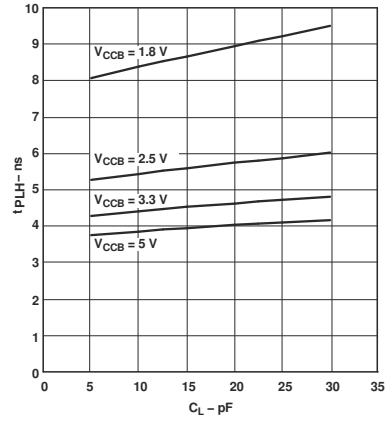


図 5-2. Typical Propagation Delay of Low-to-High (A to B) vs Load Capacitance $T_A = 25^\circ\text{C}$, $V_{CCA} = 1.8\text{V}$

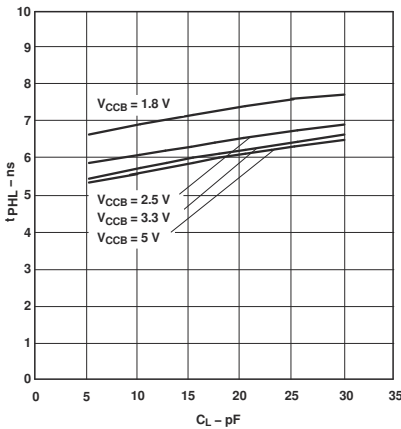


図 5-3. Typical Propagation Delay of High-to-Low (B to A) vs Load Capacitance $T_A = 25^\circ\text{C}$, $V_{CCA} = 1.8\text{V}$

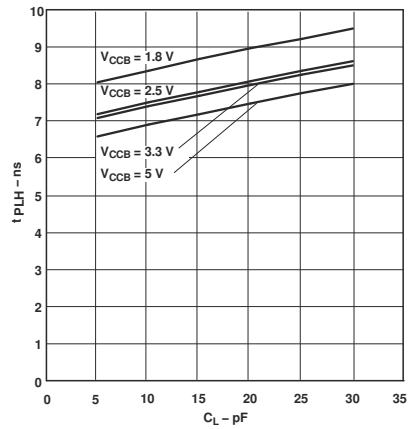


図 5-4. Typical Propagation Delay of Low-to-High (B to A) vs Load Capacitance $T_A = 25^\circ\text{C}$, $V_{CCA} = 1.8\text{V}$

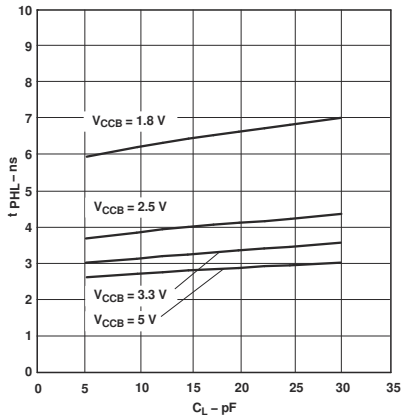


図 5-5. Typical Propagation Delay of High-to-Low (A to B) vs Load Capacitance $T_A = 25^\circ\text{C}$, $V_{CCA} = 2.5\text{V}$

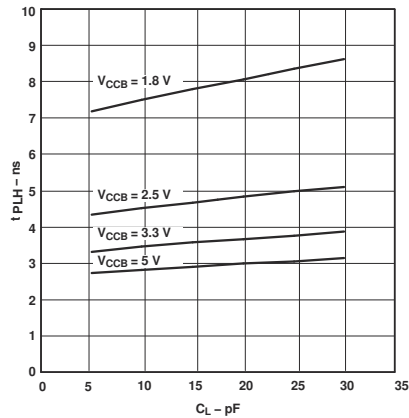


図 5-6. Typical Propagation Delay of Low-to-High (A to B) vs Load Capacitance $T_A = 25^\circ\text{C}$, $V_{CCA} = 2.5\text{V}$

5.11 Typical Characteristics (continued)

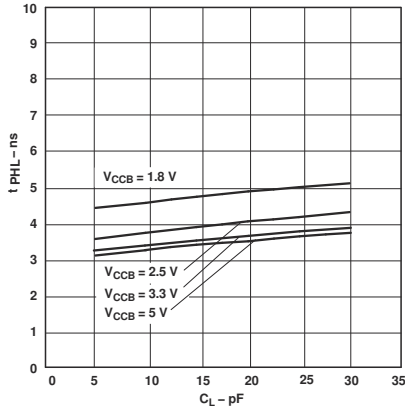


図 5-7. Typical Propagation Delay of High-to-Low (B to A) vs Load Capacitance $T_A = 25^\circ\text{C}$, $V_{CCA} = 2.5\text{V}$

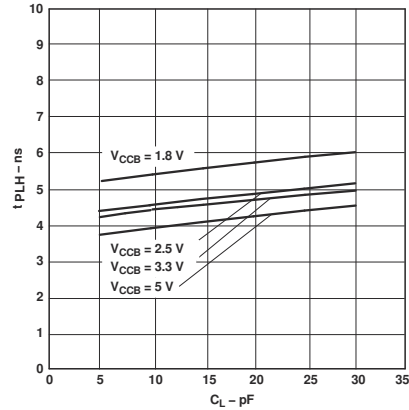


図 5-8. Typical Propagation Delay of Low-to-High (B to A) vs Load Capacitance $T_A = 25^\circ\text{C}$, $V_{CCA} = 2.5\text{V}$

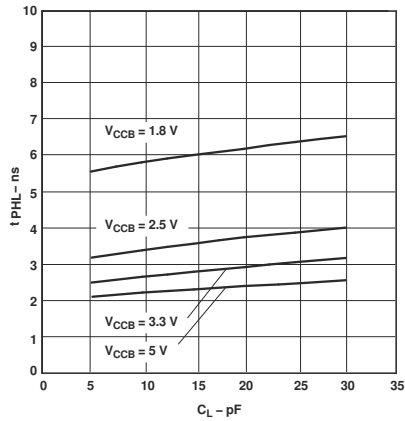


図 5-9. Typical Propagation Delay of High-to-Low (A to B) vs Load Capacitance $T_A = 25^\circ\text{C}$, $V_{CCA} = 3.3\text{V}$

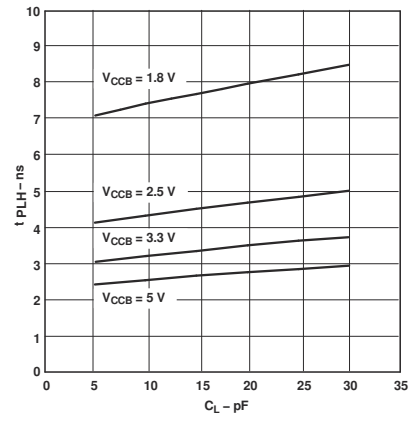


図 5-10. Typical Propagation Delay of Low-to-High (A to B) vs Load Capacitance $T_A = 25^\circ\text{C}$, $V_{CCA} = 3.3\text{V}$

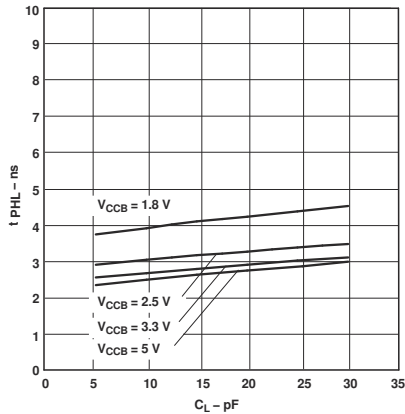


図 5-11. Typical Propagation Delay of High-to-Low (B to A) vs Load Capacitance $T_A = 25^\circ\text{C}$, $V_{CCA} = 3.3\text{V}$

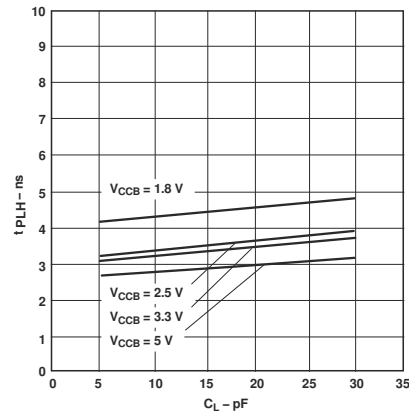


図 5-12. Typical Propagation Delay of Low-to-High (B to A) vs Load Capacitance $T_A = 25^\circ\text{C}$, $V_{CCA} = 3.3\text{V}$

5.11 Typical Characteristics (continued)

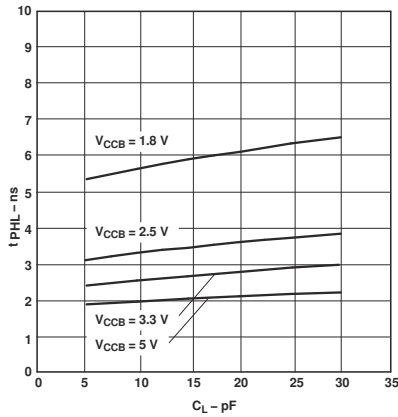


図 5-13. Typical Propagation Delay of High-to-Low (A to B) vs Load Capacitance $T_A = 25^\circ\text{C}$, $V_{CCA} = 5\text{V}$

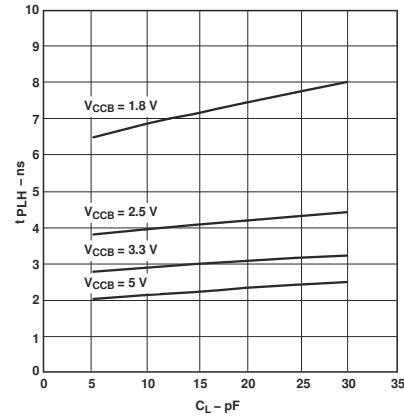


図 5-14. Typical Propagation Delay of Low-to-High (A to B) vs Load Capacitance $T_A = 25^\circ\text{C}$, $V_{CCA} = 5\text{V}$

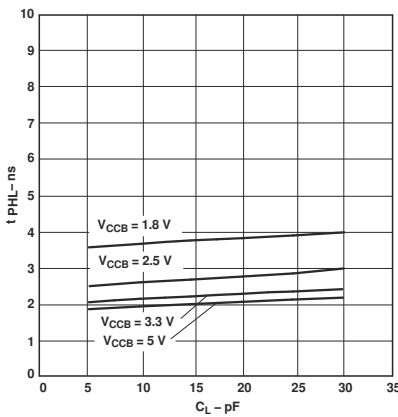


図 5-15. Typical Propagation Delay of High-to-Low (B to A) vs Load Capacitance $T_A = 25^\circ\text{C}$, $V_{CCA} = 5\text{V}$

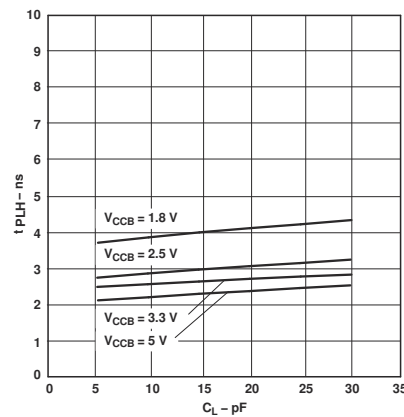
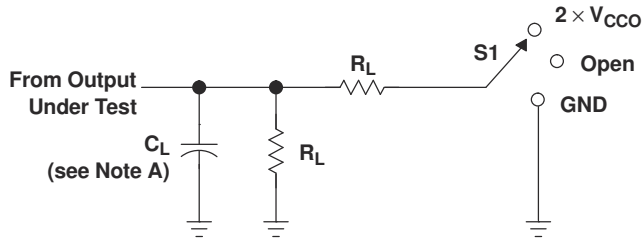


図 5-16. Typical Propagation Delay of Low-to-High (B to A) vs Load Capacitance $T_A = 25^\circ\text{C}$, $V_{CCA} = 5\text{V}$

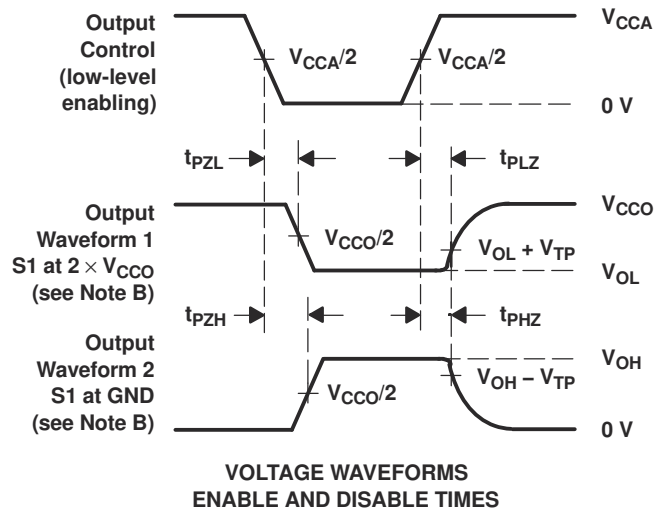
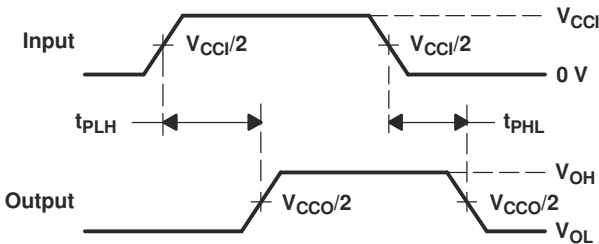
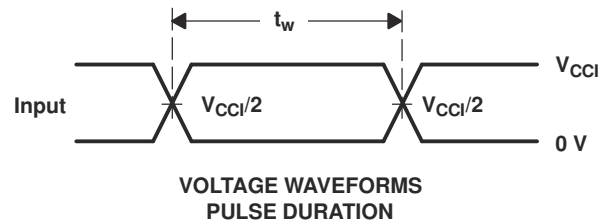
6 Parameter Measurement Information



LOAD CIRCUIT

V_{CCO}	C_L	R_L	V_{TP}
$1.8\text{ V} \pm 0.15\text{ V}$	15 pF	2 k Ω	0.15 V
$2.5\text{ V} \pm 0.2\text{ V}$	15 pF	2 k Ω	0.15 V
$3.3\text{ V} \pm 0.3\text{ V}$	15 pF	2 k Ω	0.3 V
$5\text{ V} \pm 0.5\text{ V}$	15 pF	2 k Ω	0.3 V

TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	$2 \times V_{CCO}$
t_{PHZ}/t_{PZH}	GND



- NOTES:
- C_L includes probe and jig capacitance.
 - Waveform 1 is for an output with internal conditions such that the output is low, except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high, except when disabled by the output control.
 - All input pulses are supplied by generators having the following characteristics: $PRR \leq 10\text{ MHz}$, $Z_O = 50\ \Omega$, $dv/dt \geq 1\text{ V/ns}$.
 - The outputs are measured one at a time, with one transition per measurement.
 - t_{PLZ} and t_{PHZ} are the same as t_{dis} .
 - t_{PZL} and t_{PZH} are the same as t_{en} .
 - t_{PLH} and t_{PHL} are the same as t_{pd} .
 - V_{CCI} is the V_{CC} associated with the input port.
 - V_{CCO} is the V_{CC} associated with the output port.
 - All parameters and waveforms are not applicable to all devices.

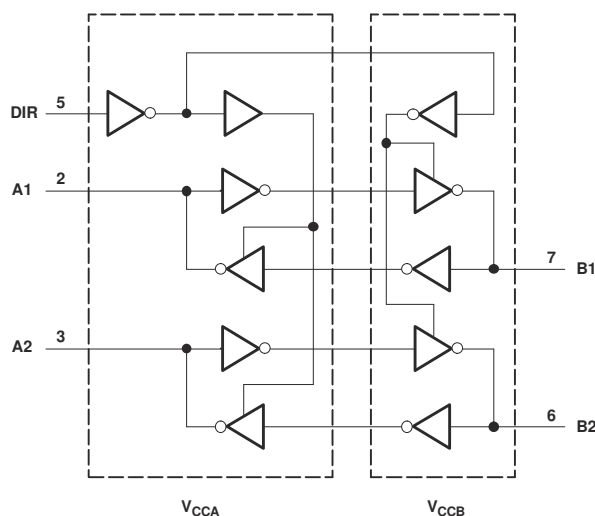
图 6-1. Load Circuit and Voltage Waveforms

7 Detailed Description

7.1 Overview

The SN74LVC2T45 is a dual-bit, dual-supply noninverting voltage level translation device. V_{CCA} supports pin Ax and the direction control pin, and V_{CCB} supports pin Bx. The A port can accept I/O voltages ranging from 1.65V to 5.5V, while the B port can accept I/O voltages from 1.65V to 5.5V. The high on DIR allows data transmission from A to B and a low on DIR allows data transmission from B to A.

7.2 Functional Block Diagram



7-1. Logic Diagram (Positive Logic)

7.3 Feature Description

7.3.1 Fully Configurable Dual-Rail Design Allows Each Port to Operate Over the Full 1.65V to 5.5V Power-Supply Range

Both V_{CCA} and V_{CCB} can be supplied at any voltage between 1.65V and 5.5V making the device suitable for translating between any of the voltage nodes (1.8V, 2.5V, 3.3V, and 5V).

7.3.2 Support High-Speed Translation

SN74LVC2T45 can support high data rate applications. The translated signal data rate can be up to 420Mbps when signal is translated from 3.3V to 5V.

7.3.3 I_{off} Supports Partial-Power-Down Mode Operation

I_{off} will prevent backflow current by disabling I/O output circuits when the device is in Partial-Power-Down mode. The inputs and outputs for this device enter a high-impedance state when the device is powered down, inhibiting current backflow into the device. The maximum leakage into or out of any input or output pin on the device is specified by I_{off} in the *Electrical Characteristics*.

7.3.4 Balanced High-Drive CMOS Push-Pull Outputs

A balanced output allows the device to sink and source similar currents. The high drive capability of this device creates fast edges into light loads so impedance matching and load conditions should be considered to prevent ringing. Additionally, the outputs of this device are capable of driving larger currents than the device can sustain without being damaged. Two outputs can be connected together for a stronger output drive strength. The electrical and thermal limits defined in the [Absolute Maximum Ratings](#) must be followed at all times.

7.3.5 Glitch-Free Power Supply Sequencing

Either supply rail may be powered on or off in any order without producing a glitch on the I/Os (that is, where the output erroneously transitions to VCC when it should be held low or vice versa). Glitches of this nature can be misinterpreted by a peripheral as a valid data bit, which could trigger a false device reset of the peripheral, a false device configuration of the peripheral, or even a false data initialization by the peripheral.

7.3.6 V_{CC} Isolation

The I/Os of both ports will enter a high-impedance state when either of the supplies are at GND, while the other supply is still connected to the device. The maximum leakage into or out of any input or output pin on the device is specified by I_{off} in the *Electrical Characteristics*.

7.4 Device Functional Modes

表 7-1 lists the functional modes of the SN74LVC2T45 device.

表 7-1. Function Table (Each Transceiver) ⁽¹⁾

INPUT DIR	OPERATION
L	B data to A bus
H	A data to B bus

(1) Input circuits of the data I/Os always are active.

8 Application and Implementation

注

以下のアプリケーション情報は、TI の製品仕様に含まれるものではなく、TI ではその正確性または完全性を保証いたしません。個々の目的に対する製品の適合性については、お客様の責任で判断していただくこととなります。お客様は自身の設計実装を検証しテストすることで、システムの機能を確認する必要があります。

8.1 Application Information

The SN74LVC2T45 device can be used in level-translation applications for interfacing devices or systems operating at different interface voltages with one another. The maximum data rate can be up to 420Mbps when the device translates signal from 3.3V to 5V. It is recommended to tie all unused I/Os to GND. The device should not have any floating I/Os when changing translation direction.

8.2 Typical Applications

8.2.1 Unidirectional Logic Level-Shifting Application

図 8-1 shows an example of the SN74LVC2T45 being used in a unidirectional logic level-shifting application.

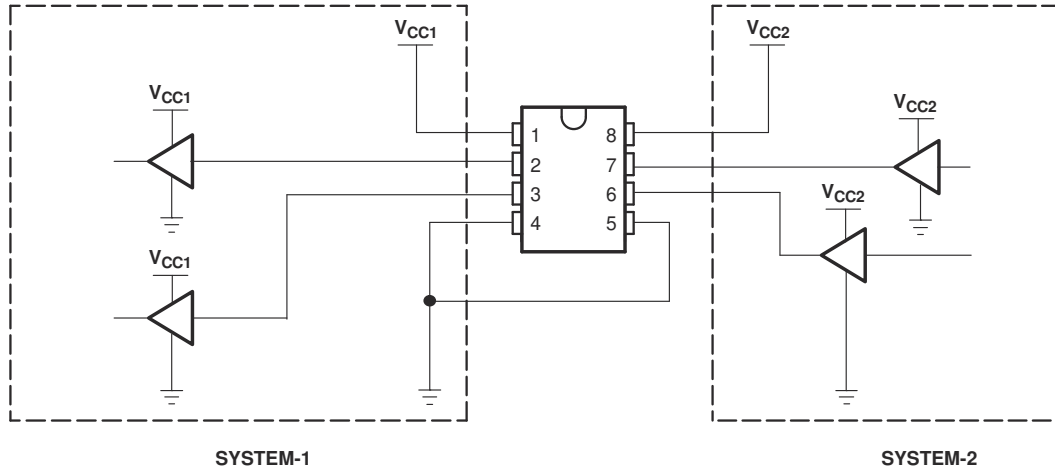


図 8-1. Unidirectional Logic Level-Shifting Application

8.2.1.1 Design Requirements

表 8-1 lists the pins and pin descriptions of the SN74LVC2T45 connections with SYSTEM-1 and SYSTEM-2.

表 8-1. SN74LVC2T45 Pin Connections With SYSTEM-1 and SYSTEM-2

PIN	NAME	FUNCTION	DESCRIPTION
1	V _{CCA}	V _{CC1}	SYSTEM-1 supply voltage (1.65V to 5.5V)
2	A1	OUT1	Output level depends on V _{CC1} voltage.
3	A2	OUT2	Output level depends on V _{CC1} voltage.
4	GND	GND	Device GND
5	DIR	DIR	GND (low level) determines B-port to A-port direction.
6	B2	IN2	Input threshold value depends on V _{CC2} voltage.
7	B1	IN1	Input threshold value depends on V _{CC2} voltage.
8	V _{CCB}	V _{CC2}	SYSTEM-2 supply voltage (1.65V to 5.5V)

For this design example, use the parameters listed in 表 8-2.

表 8-2. Design Parameters

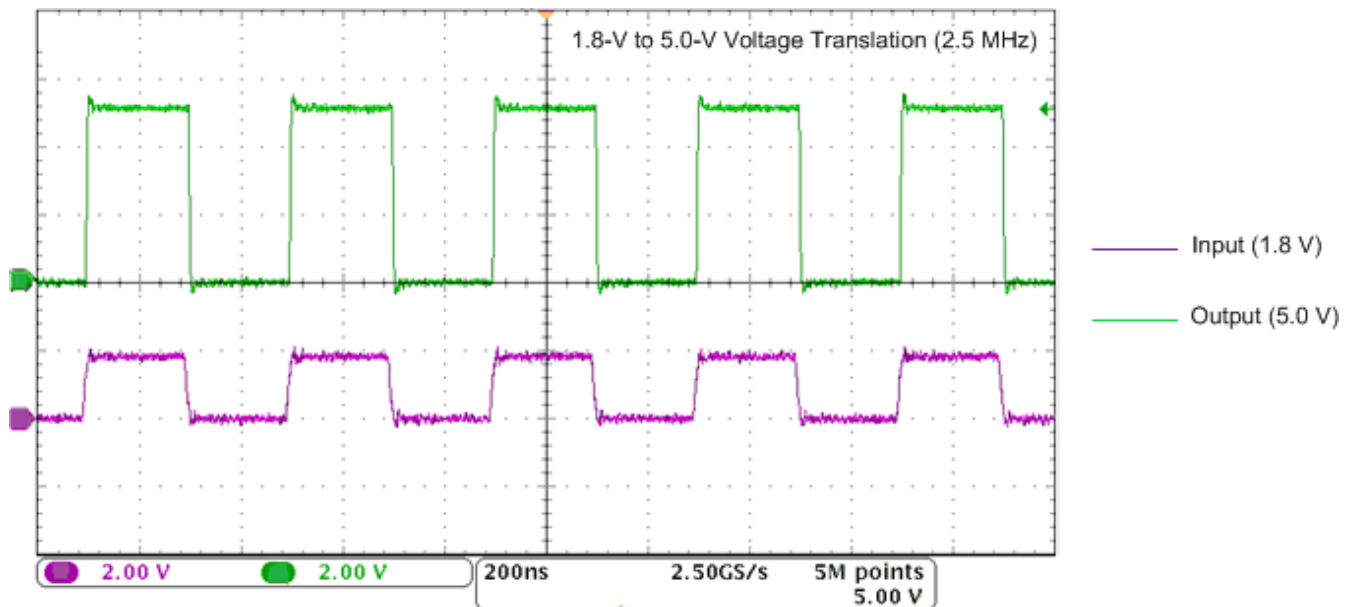
DESIGN PARAMETER	EXAMPLE VALUE
Input voltage range	1.65V to 5.5V
Output voltage range	1.65V to 5.5V

8.2.1.2 Detailed Design Procedure

To begin the design process, determine the following:

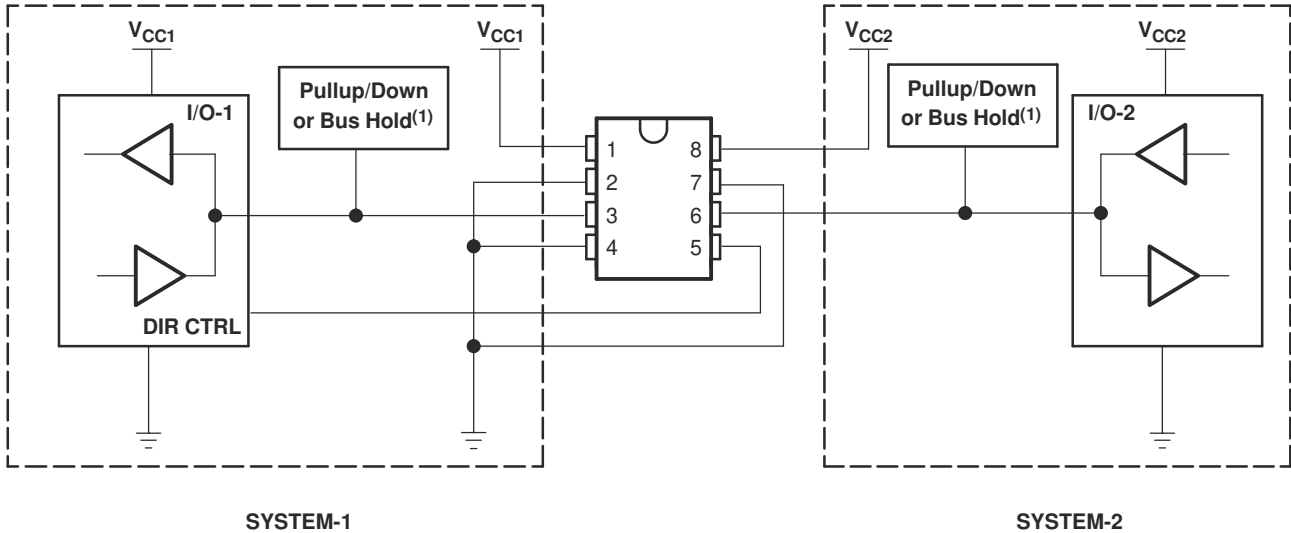
- Input voltage range
 - Use the supply voltage of the device that is driving the SN74LVC2T45 device to determine the input voltage range. For a valid logic high, the value must exceed the V_{IH} of the input port. For a valid logic low, the value must be less than the V_{IL} of the input port.
- Output voltage range
 - Use the supply voltage of the device that the SN74LVC2T45 device is driving to determine the output voltage range.

8.2.1.3 Application Curve



8.2.2 Bidirectional Logic Level-Shifting Application

☒ 8-2 shows the SN74LVC2T45 being used in a bidirectional logic level-shifting application. Because the SN74LVC2T45 does not have an output-enable (OE) pin, the system designer should take precautions to avoid bus contention between SYSTEM-1 and SYSTEM-2 when changing directions.



☒ 8-2. Bidirectional Logic Level-Shifting Application

8.2.2.1 Design Requirements

Refer to [セクション 8.2.1](#).

8.2.2.2 Detailed Design Procedure

表 8-3 provides data transmission from SYSTEM-1 to SYSTEM-2 and then from SYSTEM-2 to SYSTEM-1.

表 8-3. Data Transmission Sequence

STATE	DIR CTRL	I/O-1	I/O-2	DESCRIPTION
1	H	Out	In	SYSTEM-1 data to SYSTEM-2
2	H	Hi-Z	Hi-Z	SYSTEM-2 is getting ready to send data to SYSTEM-1. I/O-1 and I/O-2 are disabled. The bus-line state depends on pullup or pulldown. ⁽¹⁾
3	L	Hi-Z	Hi-Z	DIR bit is flipped. I/O-1 and I/O-2 still are disabled. The bus-line state depends on pullup or pulldown. ⁽¹⁾
4	L	In	Out	SYSTEM-2 data to SYSTEM-1

(1) SYSTEM-1 and SYSTEM-2 must use the same conditions, that is, both pullup or both pulldown.

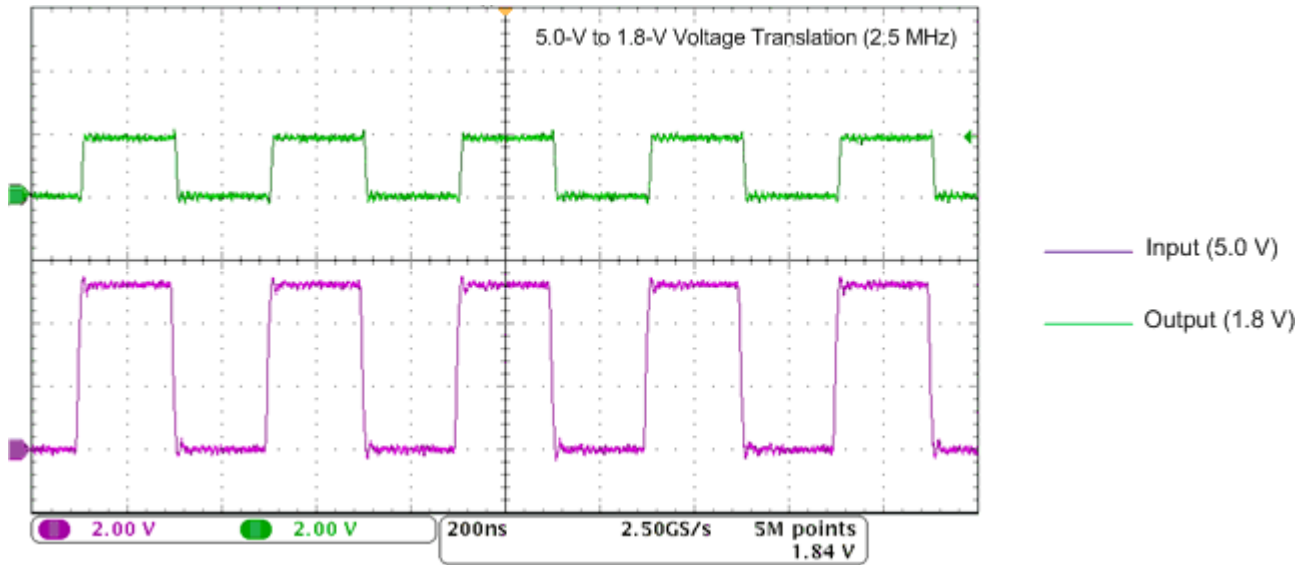
8.2.2.2.1 Enable Times

Calculate the enable times for the SN74LVC2T45 using the following formulas:

- $t_{PZH} \text{ (DIR to A)} = t_{PLZ} \text{ (DIR to B)} + t_{PLH} \text{ (B to A)}$
- $t_{PZL} \text{ (DIR to A)} = t_{PHZ} \text{ (DIR to B)} + t_{PHL} \text{ (B to A)}$
- $t_{PZH} \text{ (DIR to B)} = t_{PLZ} \text{ (DIR to A)} + t_{PLH} \text{ (A to B)}$
- $t_{PZL} \text{ (DIR to B)} = t_{PHZ} \text{ (DIR to A)} + t_{PHL} \text{ (A to B)}$

In a bidirectional application, these enable times provide the maximum delay from the time the DIR bit is switched until an output is expected. For example, if the SN74LVC2T45 initially is transmitting from A to B, then the DIR bit is switched; the B port of the device must be disabled before presenting it with an input. After the B port has been disabled, an input signal applied to it appears on the corresponding A port after the specified propagation delay.

8.2.2.3 Application Curve



8.3 Power Supply Recommendations

Always apply a ground reference to the GND pins first. This device is designed for glitch free power sequencing without any supply sequencing requirements such as ramp order or ramp rate.

This device was designed with various power supply sequencing methods in mind to help prevent unintended triggering of downstream devices, as described in [Glitch-free Power Supply Sequencing](#).

8.3.1 Power-Up Consideration

Each V_{CC} pin must have a good bypass capacitor to prevent power disturbance. For devices with a single supply, 0.1 μ F is recommended. If there are multiple V_{CC} pins, 0.01 μ F or 0.022 μ F is recommended for each power pin. It is acceptable to parallel multiple bypass capacitors to reject different frequencies of noise. 0.1 μ F and 1 μ F capacitors are commonly used in parallel. The bypass capacitor must be installed as close to the power pin as possible for best results.

表 8-4. Typical Total Static Power Consumption ($I_{CCA} + I_{CCB}$)

V_{CCB}	V_{CCA}					UNIT
	0V	1.8V	2.5V	3.3V	5V	
0V	0	< 1	< 1	< 1	< 1	μ A
1.8V	< 1	< 2	< 2	< 2	2	
2.5V	< 1	< 2	< 2	< 2	< 2	
3.3V	< 1	< 2	< 2	< 2	< 2	
5V	< 1	2	< 2	< 2	< 2	

8.4 Layout

8.4.1 Layout Guidelines

It is recommended to follow common printed-circuit board layout guidelines for device reliability, such as the follows:

- Use bypass capacitors on the power supplies.
- Use short trace lengths to avoid excessive loading.
- Place pads on the signal paths for loading capacitors or pullup resistors to help adjust rise and fall times of signals depending on the system requirements.

8.4.2 Layout Example

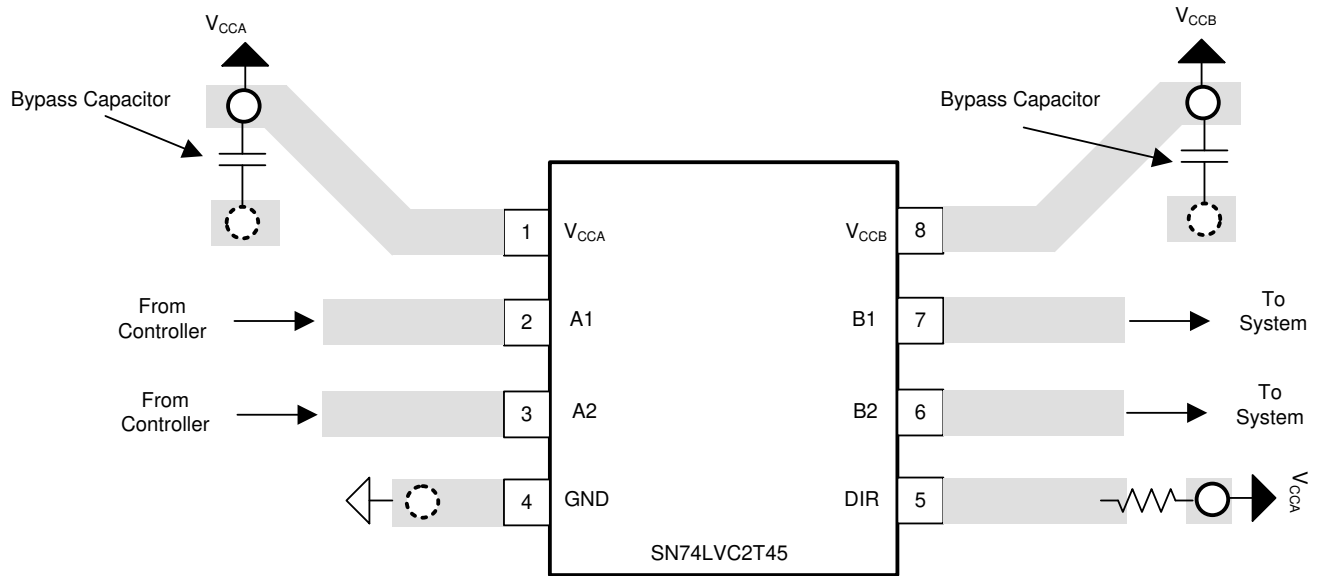
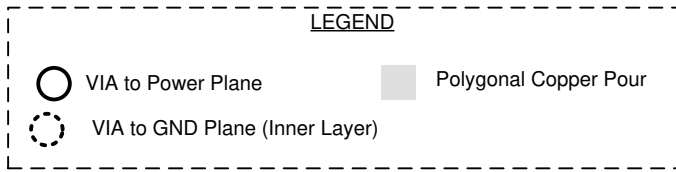


図 8-3. SN74LVC2T45 Layout Example

9 Device and Documentation Support

9.1 Documentation Support

9.1.1 Related Documentation

For related documentation, see the following:

- Texas Instruments, [Implications of Slow or Floating CMOS Inputs application note](#)
- Texas Instruments, [Designing with SN74LVCXT245 and SN74LVCHXT245 Family of Direction controlled voltage translators application note](#)

9.2 ドキュメントの更新通知を受け取る方法

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[テキサス・インスツルメンツ用語集](#) この用語集には、用語や略語の一覧および定義が記載されています。

10 Revision History

資料番号末尾の英字は改訂を表しています。その改訂履歴は英語版に準じています。

Changes from Revision M (October 2022) to Revision N (June 2024)	Page
• Updated the <i>Power Supply Recommendations</i> section.....	19

Changes from Revision L (October 2022) to Revision M (October 2022)	Page
• Changed the T_A operating free-air temperature back to 85°C	4

11 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

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PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead finish/ Ball material (6)	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
SN74LVC2T45DCTR	ACTIVE	SSOP	DCT	8	3000	RoHS & Green	SN	Level-1-260C-UNLIM	-40 to 85	CT2 (R, Z)	Samples
SN74LVC2T45DCTRE4	ACTIVE	SSOP	DCT	8	3000	RoHS & Green	SN	Level-1-260C-UNLIM	-40 to 85	CT2 (R, Z)	Samples
SN74LVC2T45DCTT	ACTIVE	SSOP	DCT	8	250	RoHS & Green	SN	Level-1-260C-UNLIM	-40 to 85	CT2 (R, Z)	Samples
SN74LVC2T45DCTTG4	ACTIVE	SSOP	DCT	8	250	RoHS & Green	SN	Level-1-260C-UNLIM	-40 to 85	CT2 (R, Z)	Samples
SN74LVC2T45DCUR	ACTIVE	VSSOP	DCU	8	3000	RoHS & Green	SN	Level-1-260C-UNLIM	-40 to 85	(CT2J, CT2Q, CT2R, T2) CZ	Samples
SN74LVC2T45DCURE4	ACTIVE	VSSOP	DCU	8	3000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	CT2R	Samples
SN74LVC2T45DCURG4	ACTIVE	VSSOP	DCU	8	3000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	CT2R	Samples
SN74LVC2T45DCUT	ACTIVE	VSSOP	DCU	8	250	RoHS & Green	SN	Level-1-260C-UNLIM	-40 to 85	(CT2J, CT2Q, CT2R, T2) CZ	Samples
SN74LVC2T45DCUTG4	ACTIVE	VSSOP	DCU	8	250	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	CT2R	Samples
SN74LVC2T45YZPR	ACTIVE	DSBGA	YZP	8	3000	RoHS & Green	SNAGCU	Level-1-260C-UNLIM	-40 to 85	(TB, TB7, TBN)	Samples

(1) The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSELETE: TI has discontinued the production of the device.

(2) **RoHS:** TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

Green: TI defines "Green" to mean the content of Chlorine (Cl) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

- (3) MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.
- (4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.
- (5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.
- (6) Lead finish/Ball material - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

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OTHER QUALIFIED VERSIONS OF SN74LVC2T45 :

- Automotive : [SN74LVC2T45-Q1](#)
- Enhanced Product : [SN74LVC2T45-EP](#)

NOTE: Qualified Version Definitions:

- Automotive - Q100 devices qualified for high-reliability automotive applications targeting zero defects
- Enhanced Product - Supports Defense, Aerospace and Medical Applications

TAPE AND REEL INFORMATION



QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal

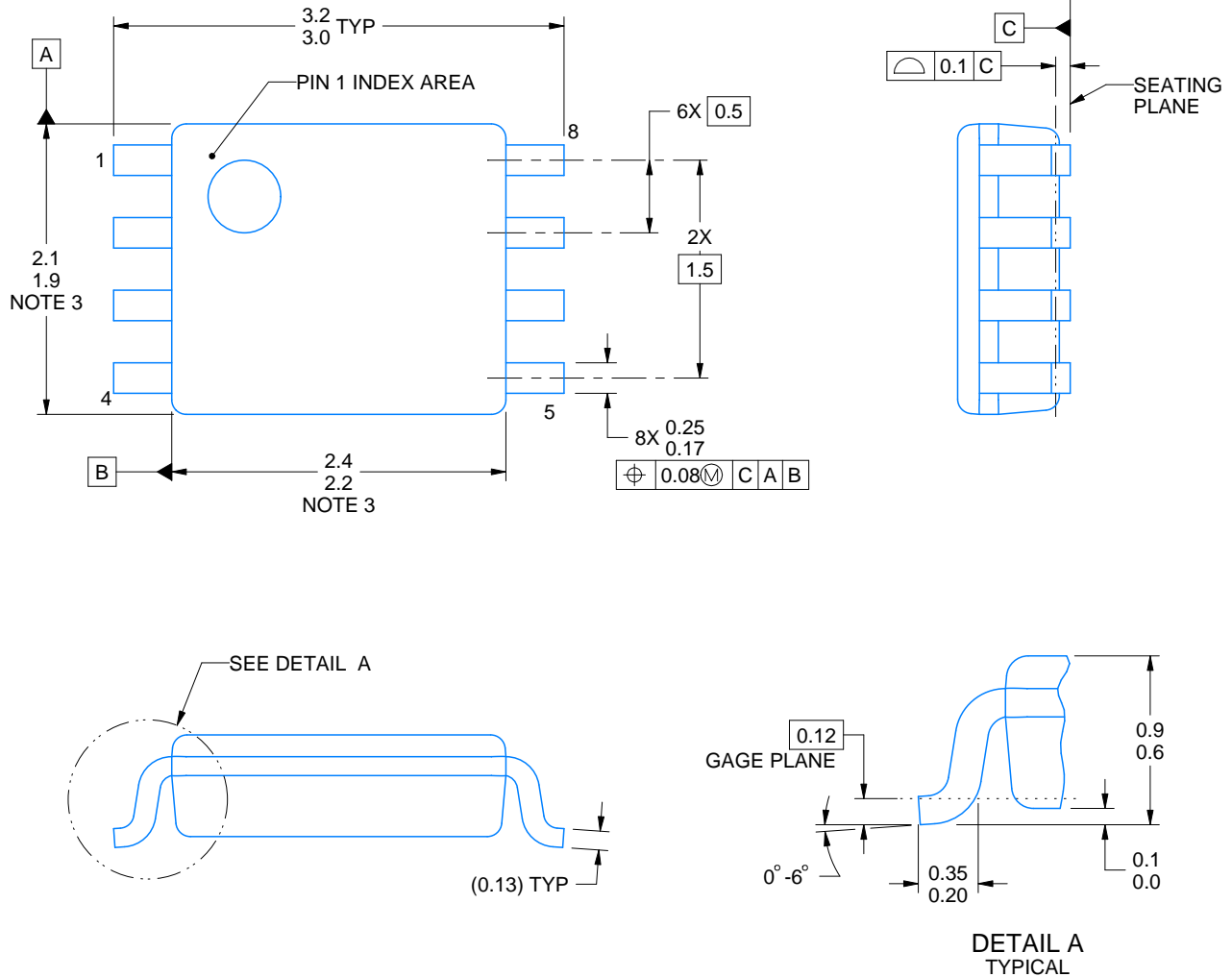
Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
SN74LVC2T45DCTR	SSOP	DCT	8	3000	180.0	12.4	3.15	4.35	1.55	4.0	12.0	Q3
SN74LVC2T45DCTT	SSOP	DCT	8	250	180.0	12.4	3.15	4.35	1.55	4.0	12.0	Q3
SN74LVC2T45DCUR	VSSOP	DCU	8	3000	178.0	9.0	2.25	3.35	1.05	4.0	8.0	Q3
SN74LVC2T45DCURG4	VSSOP	DCU	8	3000	178.0	9.0	2.25	3.35	1.05	4.0	8.0	Q3
SN74LVC2T45DCUT	VSSOP	DCU	8	250	178.0	9.0	2.25	3.35	1.05	4.0	8.0	Q3
SN74LVC2T45DCUTG4	VSSOP	DCU	8	250	180.0	8.4	2.25	3.35	1.05	4.0	8.0	Q3
SN74LVC2T45YZPR	DSBGA	YZP	8	3000	180.0	8.4	1.02	2.02	0.63	4.0	8.0	Q1

TAPE AND REEL BOX DIMENSIONS



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
SN74LVC2T45DCTR	SSOP	DCT	8	3000	190.0	190.0	30.0
SN74LVC2T45DCTT	SSOP	DCT	8	250	190.0	190.0	30.0
SN74LVC2T45DCUR	VSSOP	DCU	8	3000	180.0	180.0	18.0
SN74LVC2T45DCURG4	VSSOP	DCU	8	3000	180.0	180.0	18.0
SN74LVC2T45DCUT	VSSOP	DCU	8	250	180.0	180.0	18.0
SN74LVC2T45DCUTG4	VSSOP	DCU	8	250	202.0	201.0	28.0
SN74LVC2T45YZPR	DSBGA	YZP	8	3000	182.0	182.0	20.0



4225266/A 09/2014

NOTES:

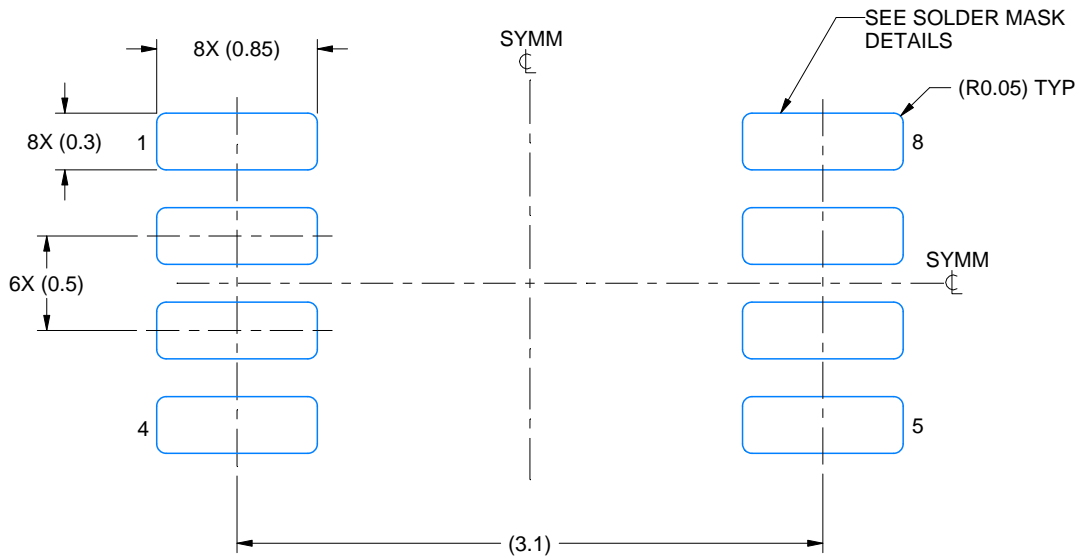
1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.15 mm per side.
4. Reference JEDEC registration MO-187 variation CA.

EXAMPLE BOARD LAYOUT

DCU0008A

VSSOP - 0.9 mm max height

SMALL OUTLINE PACKAGE



LAND PATTERN EXAMPLE
EXPOSED METAL SHOWN
SCALE: 25X



4225266/A 09/2014

NOTES: (continued)

- 5. Publication IPC-7351 may have alternate designs.
- 6. Solder mask tolerances between and around signal pads can vary based on board fabrication site.

EXAMPLE STENCIL DESIGN

DCU0008A

VSSOP - 0.9 mm max height

SMALL OUTLINE PACKAGE



SOLDER PASTE EXAMPLE
BASED ON 0.125 mm THICK STENCIL
SCALE: 25X

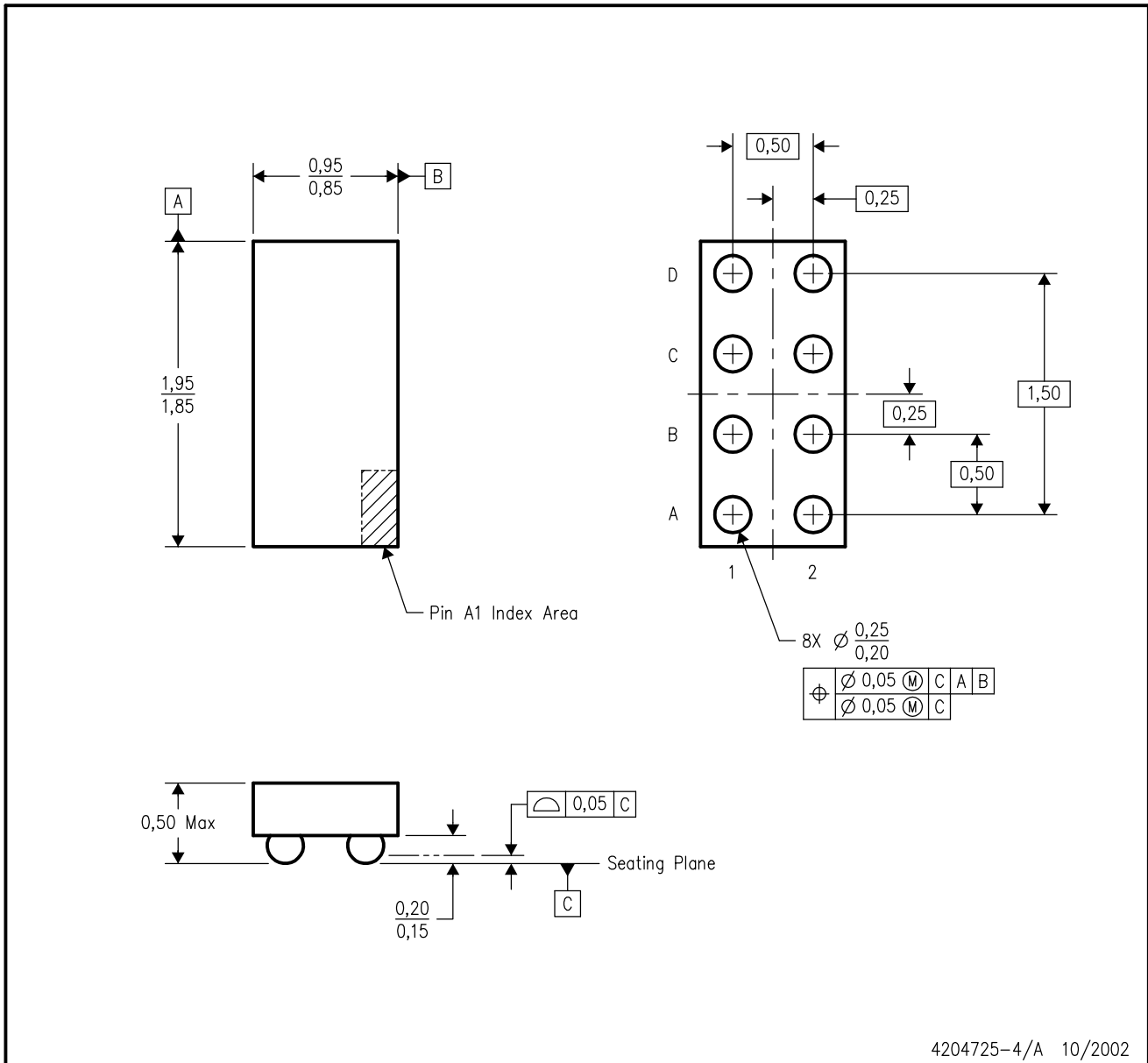
4225266/A 09/2014

NOTES: (continued)

7. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
8. Board assembly site may have different recommendations for stencil design.

YEP (R-XBGA-N8)

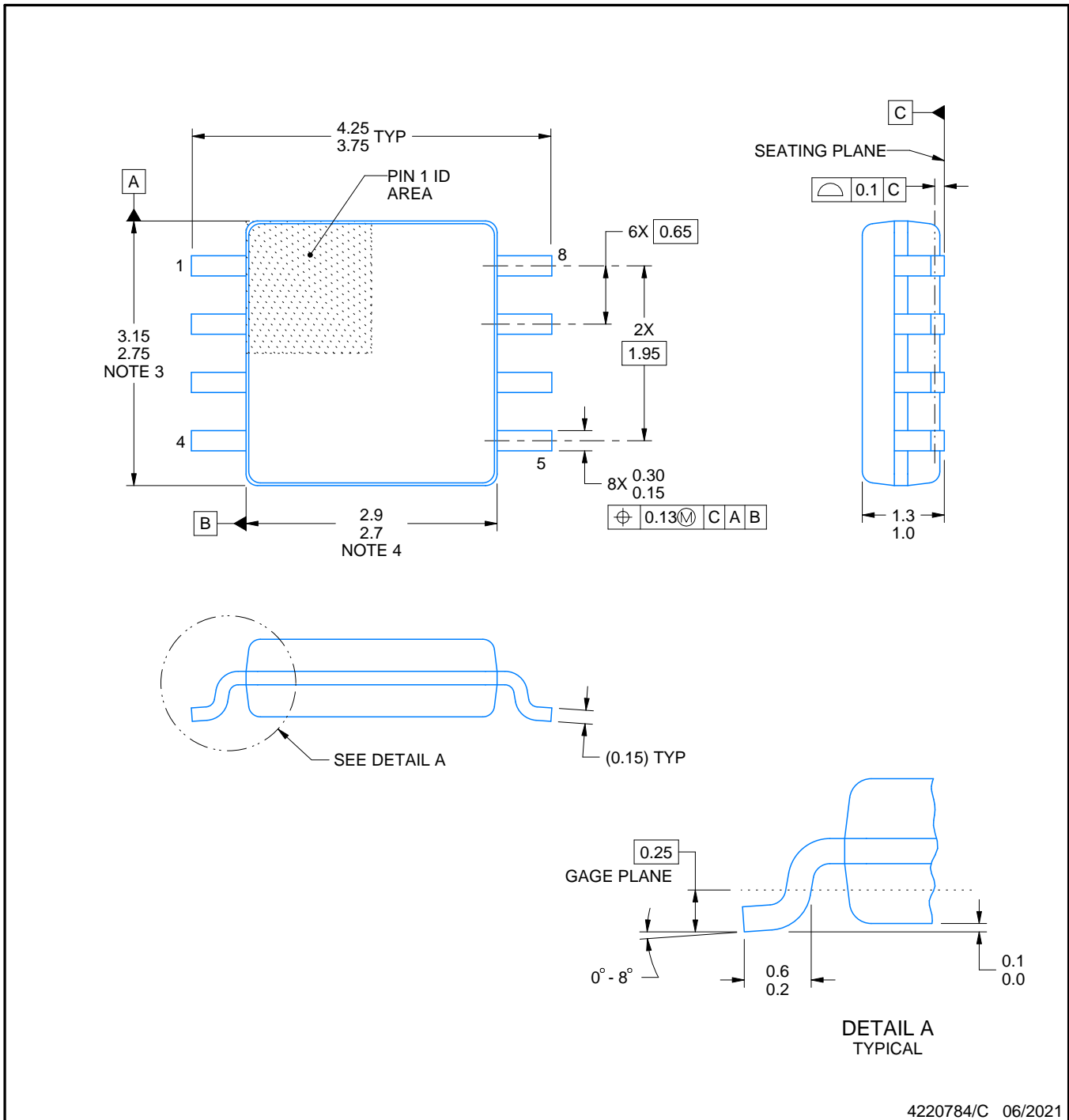
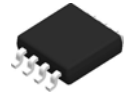
DIE-SIZE BALL GRID ARRAY



4204725-4/A 10/2002

- NOTES:
- A. All linear dimensions are in millimeters.
 - B. This drawing is subject to change without notice.
 - C. NanoStar™ package configuration.
 - D. This package is tin-lead (SnPb). Refer to the 8 YZP package (drawing 4204741) for lead-free.

NanoStar is a trademark of Texas Instruments.



4220784/C 06/2021

NOTES:

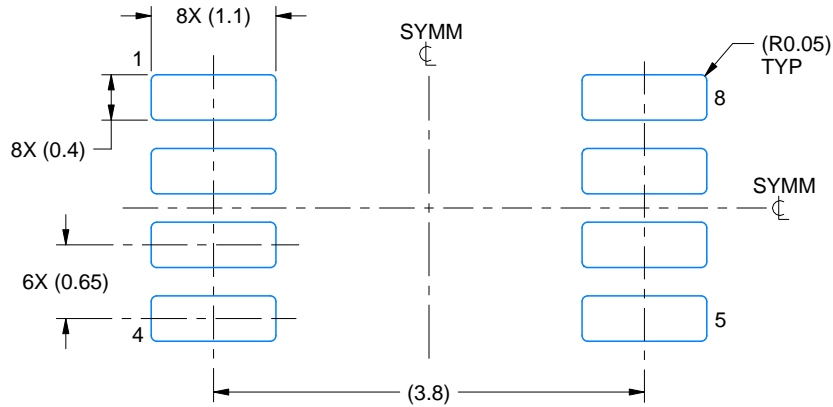
- All linear dimensions are in millimeters. Dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
- This drawing is subject to change without notice.
- This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.15 mm per side.
- This dimension does not include interlead flash. Interlead flash shall not exceed 0.25 mm per side.

EXAMPLE BOARD LAYOUT

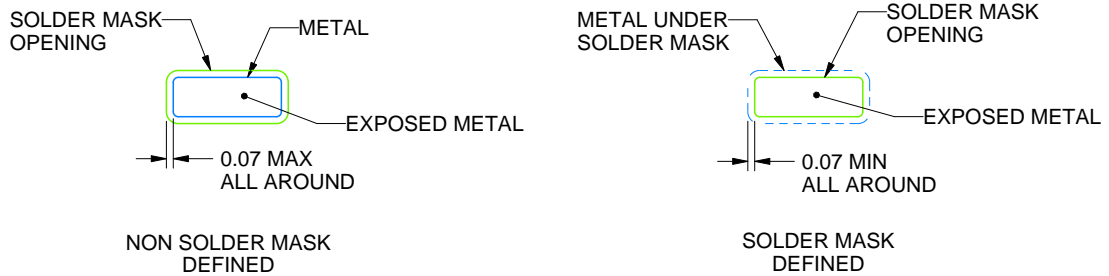
DCT0008A

SSOP - 1.3 mm max height

SMALL OUTLINE PACKAGE



LAND PATTERN EXAMPLE
EXPOSED METAL SHOWN
SCALE:15X



SOLDER MASK DETAILS

4220784/C 06/2021

NOTES: (continued)

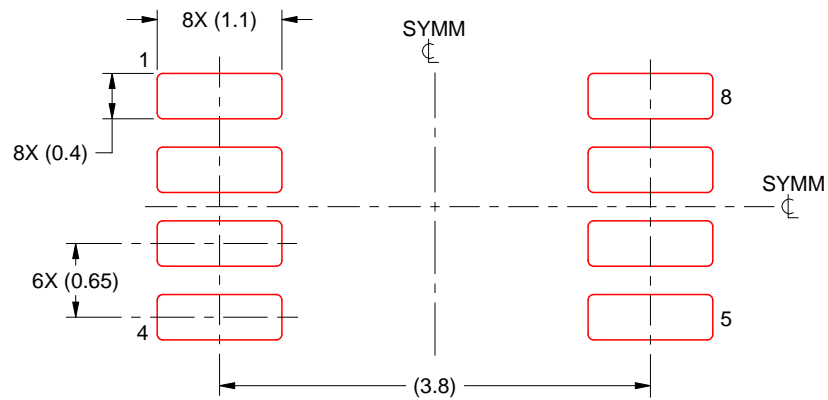
- 5. Publication IPC-7351 may have alternate designs.
- 6. Solder mask tolerances between and around signal pads can vary based on board fabrication site.

EXAMPLE STENCIL DESIGN

DCT0008A

SSOP - 1.3 mm max height

SMALL OUTLINE PACKAGE



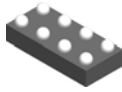
SOLDER PASTE EXAMPLE
BASED ON 0.125 mm THICK STENCIL
SCALE:15X

4220784/C 06/2021

NOTES: (continued)

7. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
8. Board assembly site may have different recommendations for stencil design.

YZP0008



PACKAGE OUTLINE

DSBGA - 0.5 mm max height

DIE SIZE BALL GRID ARRAY



D: Max = 1.918 mm, Min = 1.858 mm
E: Max = 0.918 mm, Min = 0.858 mm

4223082/A 07/2016

NOTES:

1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.

EXAMPLE BOARD LAYOUT

YZP0008

DSBGA - 0.5 mm max height

DIE SIZE BALL GRID ARRAY



LAND PATTERN EXAMPLE
SCALE:40X



SOLDER MASK DETAILS
NOT TO SCALE

4223082/A 07/2016

NOTES: (continued)

- Final dimensions may vary due to manufacturing tolerance considerations and also routing constraints. For more information, see Texas Instruments literature number SNVA009 (www.ti.com/lit/snva009).

EXAMPLE STENCIL DESIGN

YZP0008

DSBGA - 0.5 mm max height

DIE SIZE BALL GRID ARRAY



SOLDER PASTE EXAMPLE
BASED ON 0.1 mm THICK STENCIL
SCALE:40X

4223082/A 07/2016

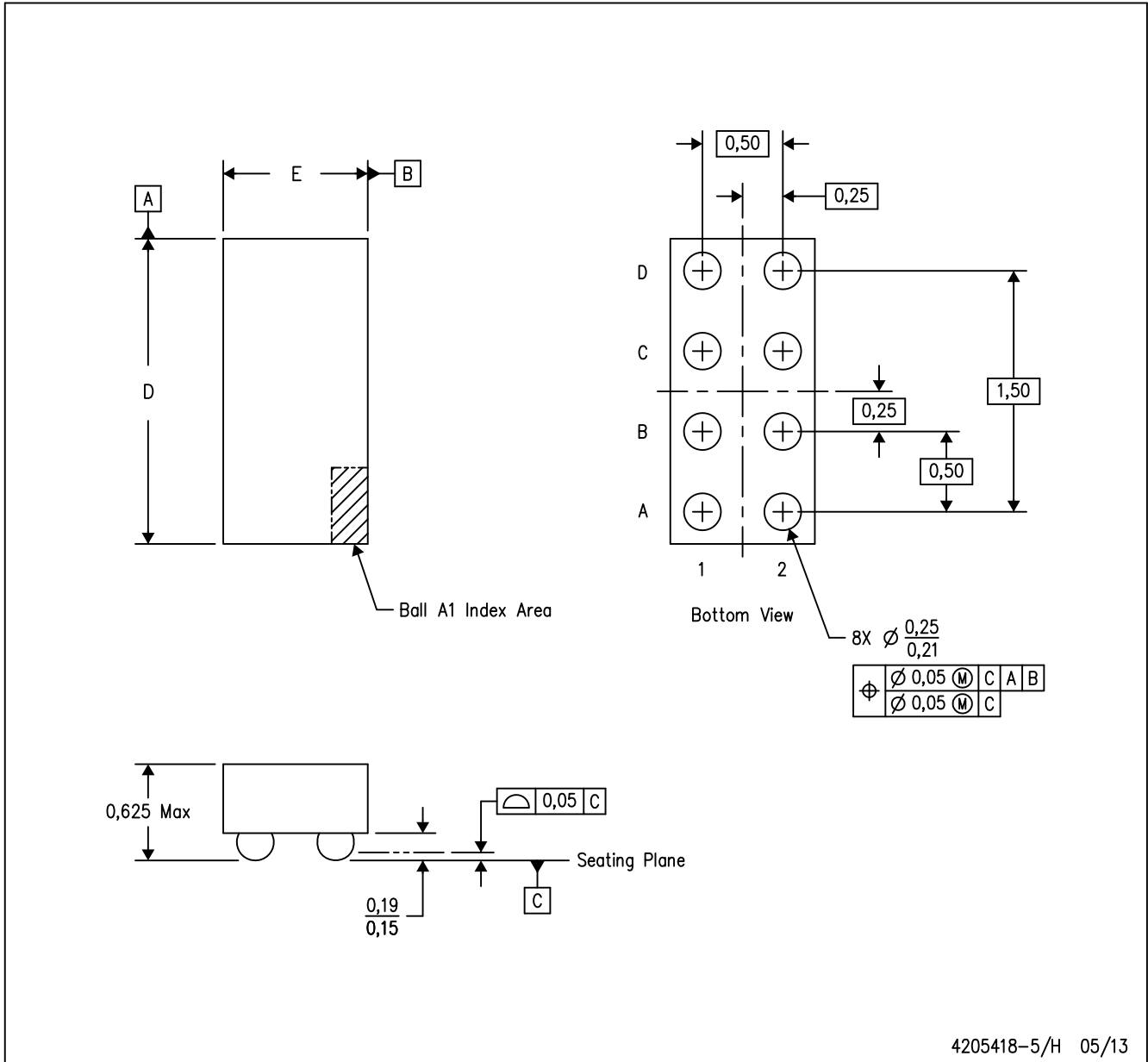
NOTES: (continued)

4. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release.

MECHANICAL DATA

YZT (R-XBGA-N8)

DIE-SIZE BALL GRID ARRAY



- NOTES:
- A. All linear dimensions are in millimeters. Dimensioning and tolerancing per ASME Y14.5M-1994.
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